



## **IRFB11N50APBF Information**



For Reference Only

Part Number IRFB11N50APBF Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 500V 11A TO-220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **Certified Quality**

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# **IRFB11N50APBF Specifications**

Manufacturer Part NumberIRFB11N50APBFManufacturerVishay SiliconixCategoryDiscrete Semiconductor ProductsPackageTO-220-3Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C11A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs52nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1423pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)170W (Tc)Rds On (Max) @ Id, Vgs520 mOhm @ 6.6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough Hole		
Category  Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single  TO-220-3  Series  TO-220-3  FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  520 mOhm @ 6.6A, 10V  Operating Temperature	Manufacturer Part Number	IRFB11N50APBF
Package         TO-220-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         11A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         52nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1423pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         170W (Tc)           Rds On (Max) @ Id, Vgs         520 mOhm @ 6.6A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)	Manufacturer	Vishay Siliconix
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Drive Voltage (Max Rds On, Min Rds On)       10V         Vgs(th) (Max) @ Id       4V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       52nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1423pF @ 25V         Vgs (Max)       ±30V         FET Feature       -         Power Dissipation (Max)       170W (Tc)         Rds On (Max) @ Id, Vgs       520 mOhm @ 6.6A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)	Drain to Source Voltage (Vdss)	500V
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Input Capacitance (Ciss) (Max) @ Vds       1423pF @ 25V         Vgs (Max)       ±30V         FET Feature       -         Power Dissipation (Max)       170W (Tc)         Rds On (Max) @ Id, Vgs       520 mOhm @ 6.6A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)	Vgs(th) (Max) @ Id	4V @ 250μA
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Rds On (Max) @ Id, Vgs       520 mOhm @ 6.6A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)	FET Feature	-
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	Power Dissipation (Max)	170W (Tc)
	Rds On (Max) @ Id, Vgs	520 mOhm @ 6.6A, 10V
Mounting Type Through Hole	Operating Temperature	-55°C ~ 150°C (TJ)
	Mounting Type	Through Hole
Supplier Device Package TO-220AB	Supplier Device Package	TO-220AB
Package / Case TO-220-3	Package / Case	TO-220-3
Report errors?		Report errors?

#### **IRFB11N50APBF** Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **IRFB11N50APBF Payment Methods**



















## **IRFB11N50APBF Shipping Methods**













If you have any question about IRFB11N50APBF, please do not hesitate to contact us!

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